AMENDMENTS TO THE CLAIMS:

The following listing of claims will replace all prior versions and listings of claims in this divisional application.

LISTING OF CLAIMS:

Claims 1-7. (Cancelled)

Claim 8. (Original) A semiconductor device with a trench isolation, comprising:

a silicon substrate having a trench on a surface thereof;

a filling layer positioned in the trench for device isolation; and

a silicon oxide layer containing healing elements positioned between the filling layer and the silicon substrate.

Claim 9. (Original) The semiconductor device with a trench isolation as claimed in claim 8, wherein the healing elements are contained in an interface boundary between the silicon oxide layer and the substrate.

Claim 10. (Original) The semiconductor device with a trench isolation as claimed in claim 8, further comprising a silicon nitride layer as an oxide barrier layer between the silicon oxide layer and the filling layer.

Claim 11. (Original) The semiconductor device with a trench isolation as claimed in claim 8, wherein the filling layer comprises a spin-on-glass layer or a CVD layer.

Claims 12-31. (Cancelled)